

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,169,632 B2
APPLICATION NO. : 10/657841
DATED : January 30, 2007
INVENTOR(S) : Johannes Baur et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Page 2, column 1, line 8,

Item [56] U.S. PATENT DOCUMENTS,

insert -- 6,291,839 B1	09/2001	Lester
3,343,026	09/1967	Luechinger et al.
5,814,839	09/1998	Hosoba
5,087,674	02/1992	Gardner et al.
2003/0116791 A1	06/2003	Baptist et al.
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6,229,160 B1	05/2001	Krames et al. --

Page 2, column 2, line 7,

Item [56] FOREIGN PATENT DOCUMENTS,

insert -- DE	199 27 945 A1	03/2000
DE	198 07 758 A1	12/1998
DE	43 24 325 A1	01/1994
DE	42 18 806 A1	12/1993
DE	27 27 508 A1	01/1979
WO	01/93310 A2	12/2001
WO	01/61765 A1	08/2001
UK	2 271 087 A	04/1994
EP	0 611 131 A1	08/1994
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EP	0 442 002 A1	08/1991
EP	0 810 674 A2	12/1997
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Page 2, column 2, line 7,

Item [56] OTHER PUBLICATIONS

insert -- J. Zhang et al. "Precise microfabrication of wide band gap semiconductors (SiC and GaN) by VUV-UV multiwavelength laser ablation", Applied Surface Science, Vol. 127-129, pp. 793-799, 1998.

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Page 2, column 2, line 7,

Item [56] OTHER PUBLICATIONS (cont'd)

W. N. Carr. "Photometric Figures of Merit for Semiconductor Luminescent Sources Operating in Spontaneous Mode", Infrared Physics, Vol. 6, pp. 1-19, 1966. --

Signed and Sealed this
Twelfth Day of June, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office